

# **IGBT**

## SGS5N150UF

## **General Description**

Fairchild's Insulated Gate Bipolar Transistor (IGBT) provides low conduction and switching losses. SGS5N150UF is designed for the Switching Power Supply applications.

### **Features**

- · High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 4.7 \text{ V}$  @  $I_C = 5A$
- High Input Impedance

## **Application**

Switching Power Supply - High Input Voltage Off-line Converter





## **Absolute Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description		SGS5N150UF	Units
V <sub>CES</sub>	Collector-Emitter Voltage		1500	V
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	10	Α
	Collector Current	@ T <sub>C</sub> = 100°C	5	Α
I <sub>CM (1)</sub>	Pulsed Collector Current		20	Α
P <sub>D</sub>	Maximum Power Dissipation	@ $T_C = 25^{\circ}C$	50	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	20	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

#### Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Cha	racteristics					
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 1mA$	1500			V
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			1.0	mA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			± 100	nA
On Chai	racteristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C = 5mA$ , $V_{CE} = V_{GE}$	2.0	3.0	4.0	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 5A, V <sub>GE</sub> = 10V		4.7	5.5	V
Dynamic Characteristics  C <sub>ies</sub> Input Capacitance Vor = 10V, Vor = 0V				780		pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 10V_{,} V_{GE} = 0V_{,}$ f = 1MHz		130		pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 = 11VII 12		70		pF
Switchir	ng Characteristics			1	-	1
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V		10		ns
t <sub>r</sub>	Rise Time	$I_{\rm C} = 5A$		15		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_{G} = 10\Omega$ $V_{GF} = 10V$		30	50	ns
t <sub>f</sub> E <sub>on</sub>	Fall Time			70	120	ns
⊨ <sub>on</sub>	Turn-On Switching Loss	Inductive Load		190		uJ
E <sub>off</sub>	Turn-Off Switching Loss	T <sub>C</sub> = 25°C		100		uJ
<b>∟</b> ts	Total Switching Loss			290	580	uJ
E <sub>ts</sub> Q <sub>g</sub> Q <sub>ge</sub>	Total Gate Charge	$V_{CF} = 600 \text{ V}, I_{C} = 5\text{A}$		30	45	nC
Q <sub>ge</sub> Q <sub>gc</sub>	Gate-Emitter Charge	$V_{GE} = 10V$		3	5	nC
$\sim$	Gate-Collector Charge	UL		15	25	nC

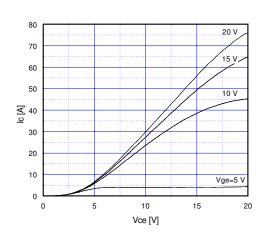


Fig 1. Typical Output Characteristics

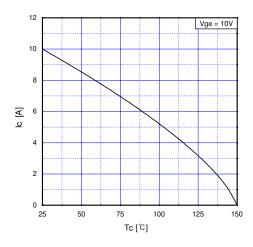


Fig 3. Maximum Collector Current vs. Case Temperature

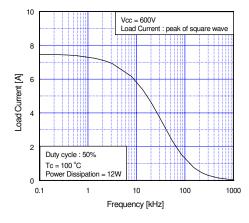


Fig 5. Load Current vs. Frequency

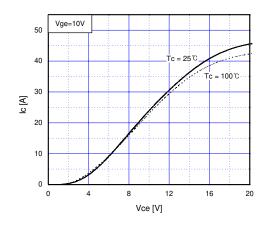


Fig 2. Typical Output Characteristics

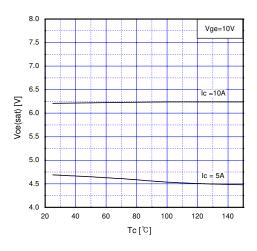


Fig 4. Saturation Voltage vs. Case Temperature

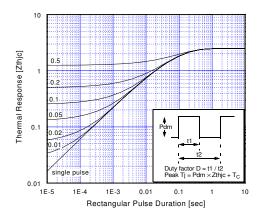


Fig 6. Transient Thermal Impedance of IGBT Junction to Case

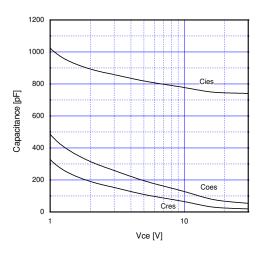


Fig 7. Typical Capacitance vs. **Collector to Emitter Voltage** 

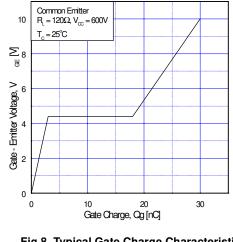


Fig 8. Typical Gate Charge Characteristic

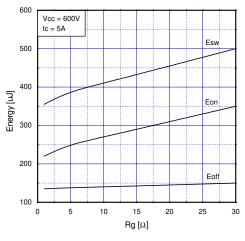


Fig 9. Typical Switching Loss vs. **Gate Resistance** 

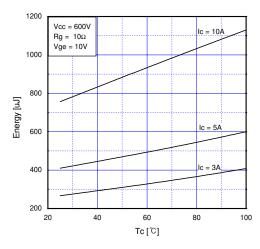


Fig 10. Typical Switching Loss vs. Case Temperature

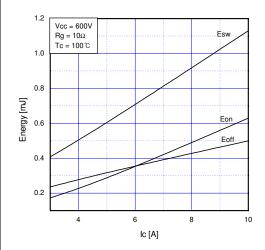


Fig 11. Typical Switching Loss vs. **Collector Current** 

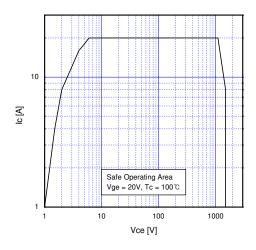
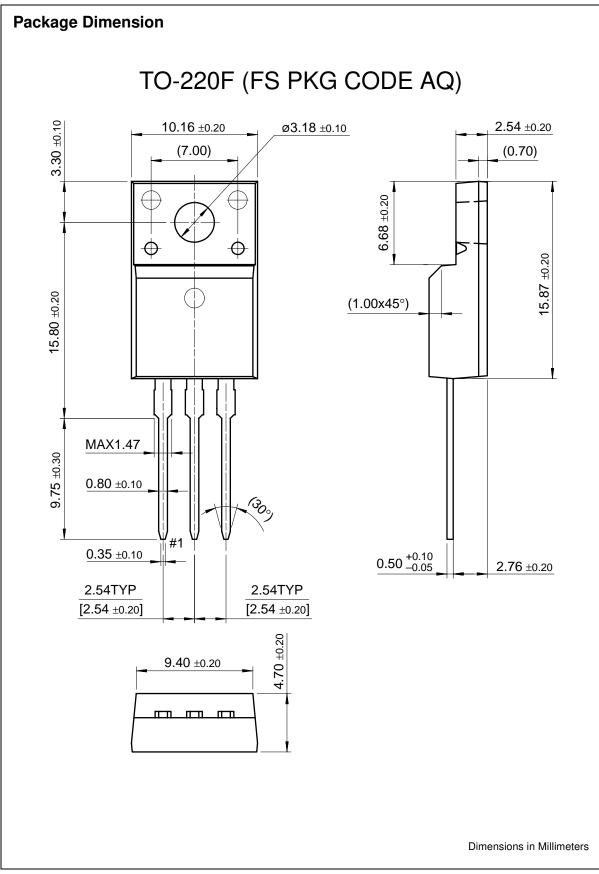


Fig 12. Turn-Off SOA



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